Drastic modification in thermal conductivity of TiCoSb Half-Heusler alloy: Phonon engineering by lattice softening and ionic polarization

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Abstract: A drastic variation in thermal conductivity (κ) for synthesized samples (TiCoSb_{1+x}, x=0.0, 0.01, 0.02, 0.03, 0.04, and 0.06) is observed and ~47% reduction in κ is reported for TiCoSb_{1.02} sample. In depth structural analysis is performed, employing mixed-phase Rietveld refinement technique. Embedded phases and vacancy are analyzed from X-ray diffraction (XRD) and Scanning electron microscopy data. Local structures of the synthesized samples are explored for the first time by X-ray absorption spectroscopy measurements for TiCoSb system and corroborated with Rietveld refinement data. Lattice dynamics are revealed using Raman Spectroscopy (RS) measurements in unprecedented attempts for TiCoSb system. XRD and RS data accomplishes that variation in κ as a function of Sb concentration is observed owing to an alteration in phonon group velocity related to lattice softening. Polar nature of TiCoSb HH sample is revealed. LO-TO splitting (related to polar optical phonon scattering) in phonon vibration is observed due to polar nature of TiCoSb synthesized samples. Tailoring in LO-TO splitting due to screening effect, correlated with Co vacancies is reported for TiCoSb_{1.02} synthesized samples. Lattice softening and LO-TO splitting lead to decreases in κ ~47% for TiCoSb_{1.02} synthesized sample.

Keywords: Thermal Conductivity, Rietveld Refinement, Scanning Electron Microscopy, EXAFS, XANES, Raman Spectroscopy, LO-TO Splitting, Lattice Softening.

I. Introduction

Thermal conductivity (κ) is one of the fundamental physical properties, involved in thermal energy transfer in a material. Enhancement or reduction in k requires various targeted objectives viz., high k for electronic cooling materials and low κ for thermoelectric (TE) materials.^{1,2} World-wide resurgence for alternative source of energy draws the attention of scientists and TE materials may play a positive role in this aspect. TE materials are those, which convert thermal energy to electrical energy.¹⁻³ However, potential alternative energy source, intriguing class of materials, and due to the unique physics involved in the technology, TE materials related investigation is one of the interesting topic for researchers.^{2,4-} 6 The performance of TE materials is judged by the dimensionless figure of merit (ZT), $ZT = S^2 \sigma T/\kappa$, where S is the Seebeck coefficient (or thermopower), σ is electrical conductivity, and κ is the total thermal conductivity (= $\kappa_e + \kappa_l$, κ_e is electronic part and κ_l is thermal part) of the system at temperature T. Difficulties in improvement of ZT arise owing to their complex dependencies and coupling amid S, σ and κ_{e} . Hence, κ_1 is the only decoupled parameter, which may be tuned to enhance the ZT.⁷ Numerous studies exist where increasing Power Factor (PF), S² σ leads to enhanced ZT.⁸⁻¹⁰ Nevertheless, commercial implementation faces obstacles due to its high κ . To date, numerous TE materials with high ZT are explored across a range of operating temperatures.¹¹⁻²¹ GeTe ^{11, 12}, PbTe based materials ^{13, 14}, and half Heusler (HH) materials ¹⁵⁻¹⁹ are well-suited TE materials for moderate temperature ranges. On the other hand, BiTe based materials²⁰ are more appropriate for room temperature applications, while Si-Ge alloys and oxide materials prove to be ideal for higher temperatures, typically exceeding 1073 K.²¹ However, applications are limited by the poor chemical, mechanical strength and thermal stability.²²

MCoSb and MNiSn (M=Ti, Hf and Zr) based HH compounds, among the numerous state-of-the-art TE materials are garnered worldwide attention as promising candidates at mid temperature TE technology. This is attributed to their narrow band gap, high substitutability of constituent elements, enhanced contact engineering, and high thermal stability at mid temperature.²³ HH alloys are in the category of XYZ type compound, where X is early transition

metal (Sc, Ti, V groups), Y is late transition metal (Fe, Co, Ni groups) i.e. less electropositive than X, and Z is main group elements.²² However, the structure may be considered as a combination of rock salt (XZ) and Zinc blande (YZ) type sublattices with cubic space group, $F\overline{4}3m$ (216).²⁴ The wyckoff position of the constituent elements i.e. X, Y, and Z are 4a (0, 0, 0), 4c $(\frac{1}{4}, \frac{1}{4}, \frac{1}{4})$ and 4b $(\frac{1}{2}, \frac{1}{2}, \frac{1}{2})$, respectively.²² The tetragonal 4d (3/4, 3/4, 3/4) site is filled for the XY₂Z Heusler alloy.²⁴ 4d site in XYZ type HH structure may be referred as the interstitial site. It is crucial to highlight that the preliminary research on the HH materials commenced in the late 1990s, identifying n-type and p-type phases with X^{IV}NiSn and $X^{IV}CoSb$ (X^{IV} = Ti, Zr, and Hf.²⁵⁻³⁰ Till now, various HH based TE materials such as TiCoSb, TiNiSn, X^{V} FeSb (X^{V} = V, Nb and Ta), NbCoSn, ZrCoBi etc.³¹⁻³⁷ are well investigated, exhibiting large S and moderate σ . However, concurrent exhibition of high κ , leads to a reduction in the overall figure-of-merit (ZT) of the materials.²³ The choice of HH material, TiCoSb is potential to be used as TE material at mid-temperature.³⁸ Narrow band gap with Fermi level on top of the valence band (p-type) and 18 valence electron count (VEC) made them promising candidates in TE power generation. TE performance of TiCoSb is commendable due to substantial S and moderate σ . However, the efficiency is limited by the high κ . Resurgence are focused to enhance the efficiency by reducing κ for TiCoSb.³⁹ Nano inclusion and complex iso-electronic alloying are important routes to enhance the efficiency of a TE material, by reducing κ .^{39, 40} Micro/nanostructuring of materials also led to a decrease in κ_{1}^{41-43} Huang et al. have reported that incorporation of 6 vol% ZrO2 nano-inclusions to the ZrNiSn HH alloy leds to a significant reduction (~35%) in κ through introduction of phonon scattering centers.44 Composite material, 2% $Zr_{0.25}Hf_{0.75}Ni_2Sn$ FH phases into the $Zr_{0.25}Hf_{0.75}NiSn$ HH reduction in κ (~20%).⁴⁵ Further, the matrix causes introduction of point defects and disorder may lead to a substantial reduction in κ through enhanced phonon scattering. Iso-electronic alloying is one of the viable approach for introducing point defects, effectively leads to a reduction in κ .⁴⁰

The effect of iso-electronic alloying, band engineering, and nanostructuring on TE properties has been extensively investigated.^{39, 40, 46} However, it is crucial to mention that, κ_1 is highly responsive to the variation in phonon dispersion, specifically the speed of phonon in material.⁴⁷ A dramatic reduction in κ is reported by G Tan et al. when alloying SnTe with AgSbTe₂, owing to a reduction in velocity of phonon.⁴⁸ In a recent study, R Hanus et al. highlighted that the induction of internal-strain-induced lattice softening proves to be a promising approach to reduce κ .⁴⁷ In this context, S. Y. Back et al. also observed reduced κ_1 of ~ 0.53 W m⁻¹ K⁻¹ at 300 K for InTe_{0.99}. This value reflects around 25% decrease in κ , compared to pristine InTe.⁴⁹ Further, introduction of

inhomogeneous internal strain fields is another approach to increase additional phonon scattering centers in the synthesized materials.47 Noteworthy, enhancement of TE efficiency by lattice softening, results from alloying or the introduction of vacancies is one of the crucial and well known approaches.^{48, 50, 51} Further, in polar material, the polar optical phonon scattering plays very promising role in electronic and thermal transport. One of the important characters in phonon transport of polar crystalline material is LO-TO splitting.^{52, 53} LO-TO splitting occurs due to the interplay between LO phonons and the long-range electric field produced by ionic polarization.⁵² It is noteworthy to mention that the polar coupling constant, for various HH TE materials (ZrCoSb~0.89, NbFeSb~0.74, ZrNiSn~0.32 etc) show higher value than other PbTe based (PbTe~0.29, PbSe~0.36) TE materials.⁵² The observation signifies that polar optical phonon scattering could play a promising role in reducing κ , specifically in HH TE materials. Furthermore, presence of defects in polar TE materials have the potential to alter the scattering centers, may influence both σ and κ . In a recent study, Ren et al. have reported anomalous phononic transport in ZrNiBi HH alloys due to the presence of vacancies.54 Substitution of Sn at Co site in ZrCoSb system enhances the intensity of phonon-phonon interaction causes reduction in k (~80%) owing to dominant role of Co/4d Frenkel point defects.55

In this maiden attempt we are trying to investigate the nature of interactions associated with phonon transport and reveal the effect of Sb concentration on κ for the previously reported samples TiCoSb_{1+x} (x=0.0, 0.01, 0.02, 0.03, 0.04, 0.06).⁵⁶ Minimum κ and corresponding highest ZT was reported for x=0.02.⁵⁶ However, lowest electron-phonon (e-ph) interaction coefficient, estimated from temperature dependent S was obtained for TiCoSb_{1.02}. Hence, it may be concluded that the estimated κ is not associated with the e-ph interaction due to the change in electronic structure. It is important to mention that highest crystalline quality with minimum embedded phases and defects were reported in the article, indicates minimum scattering centre in TiCoSb_{1.02}.⁵⁶ Therefore, further investigation is needed to enlighten the behaviour of κ in TiCoSb_{1+x} system.

A detail experimental study of lattice dynamics of TiCoSb HH alloy, as well as the role of defects and embedded phase on k and crystalline order of polycrystalline TiCoSb alloy are investigated in this article. In-depth structural characterizations using Rietveld refinement method from the x-ray diffraction (XRD) data is already reported.⁵⁶ Presence of Co vacancy, CoTi , and CoSb precipitated phases are revealed from XRD, SEM-EDS and XAS measurments. First time, detailed investigation of local structural ordered around Co-atom is reported, using XAS measurement. Crystalline order of the TiCoSb based HH TE materials is mainly preserved owing to the contribution of 2nd shell i.e., Co-Sb shell and most ordered TiCoSb sample is achieved for x=0.02. Further, first time in-depth study of lattice dynamics and vibrational spectroscopy of TiCoSb HH alloy, using the Raman spectroscopy measurement is presented in this article. Evidence of the polar nature of TiCoSb-based HH alloys is observed. A plausible explanation is provided for the polar behaviour of TiCoSb. Further, behaviour of strain (ϵ) with Sb concentration is assessed through Raman spectroscopy and XRD measurements. The correlation of crystalline strain and Co vacancies with κ is reported. Finally, about 47% reduction in κ is achieved for TiCoSb_{1.02} sample, tuning crystalline strain and Co vacancies in TiCoSb_{1+x} matrix.

In this current study, we explore TiCoSb as a functional element for effective energy conversion. TiCoSb_{1+x} (where x = 0.0, 0.01, 0.02, 0.03, 0.04, 0.06) is synthesized to investigate the impact of defects and disorder on the reduction of κ in the TiCoSb system. The key findings of the present study are (i) Co vacancies in TiCoSb unitcell increases with Sb concentration, (ii) minute amount of CoTi and CoSb embedded phases is revealed from XRD and SEM-EDS measurements (iii) most ordered TiCoSb sample is achived for x=0.02 from EXAFS studies (iv) polar behaviour of TiCoSb is observed from the LO-TO splliting of Raman spectroscopy (v) about 47% reduction in κ is achieved for TiCoSb_{1.02} sample, tuning crystalline strain and Co vacancies in TiCoSb_{1+x} matrix.

This paper is organized as follows. Section II describes precise steps for sample synthesis and characterizations to analyze the experimental results. All the experimental results are critically scruitnized and discussed in Sec. III. Finally, conclusion and correlation are drawn on the basis of experimental results in Sec. IV.

II. Experimental Details

TiCoSb_{1+x} (x=0, 0.01, 0.02, 0.03, 0.04, 0.06) samples were synthesized by solid state reaction method followed by arc melting of constituent elements. Stoichiometric amount of Ti, Co and Sb (each of purity 99.999%, Alfa Aesar, UK) were melted using an electric arc furnace at vacuum under the flow of argon atmosphere.⁵⁶ The detailed sample synthesis process is alredy reported elsewhere.⁵⁶ The structural characterization of the synthesized TiCoSb_{1+x} alloys were carried out using powder X-ray diffractometer (Model: X'Pert Powder, PANalytical) with Cu-K_α radiation of wavelength 0.15418 nm. All the X-ray diffraction (XRD) measurements were performed on powdered samples in range of $20^0 < 2\theta < 80^0$ in θ-θ geometry. In-depth structural parameters were divulged by Rietveld refinement technique using FullProf software⁵⁷ and reported in previous article.⁵⁶

X-ray absorption spectroscopy (XAS) studies were carried out to investigate the local geometric and electronic structure of matter by measuring Co K-edge absorption spectra in transmission mode (fig. S2, Supplementary Information) at

the beamline of the INDUS-2 synchrotron source (2.5 GeV, 200 mA) at the Raja Ramanna Centre for Advanced Technology (RRCAT), Indore, India. The beamline operates in the energy range of 4 keV to 25 keV with energy resolution $E/dE \sim 10$. Noteworthy to mention that, due to the range of operational energy it was not possible to take data at Sb Kedge. The beamline optics consist of a Rh/Pt coated collimating meridional cylindrical mirror followed by a Si (111) (2d = 6.2709 Å) based double crystal monochromator (DCM). For horizontal focusing the second crystal of DCM was used, which is a sagittal cylindrical crystal. One ionization chamber with a length of 300 mm and a solid-state detector were used in the setup. The photon energy scale was calibrated by measuring the XAS spectrum of a standard Co metal foil. Co K-edge data was taken in the transmission mode. The absorption coefficient μ was obtained using the relation: $\mu(E)$ \propto I₀/I_t, where I₀ is the incident X-ray intensity, and I_t is the measured transmission intensity.

Raman spectroscopic measurements (Model: inVia, Make: Renishaw, UK) were carried out at room temperature. The measurements were performed in the range 100-400 cm⁻¹, utilizing a 785 nm solid-state laser with a sub-micron focusing diameter (objective of 50x magnification). A 2400gm/cc grating was used for monochromatization with TE cooled charged coupled device (CCD) as detector in the back scattering configuration.

ZEISS EVO-MA 10 microscope equipped with tungsten filament bulb was used to collect scanning electron microscope (SEM) images. To carry out SEM the samples were drop-casted onto a glass substrate and allowed to dry at room temperature for three hours. The compositional analysis was performed by utilising an energy dispersive X-ray (EDS) attached to the instrument.

III. Results and Discussion

Structural characterization of synthesized TiCoSb_{1+x} (x=0, 0.01, 0.02, 0.03, 0.04, and 0.06) polycrystalline alloys are performed by XRD measurement 56 and all the synthesized samples are crystallized in $F\overline{4}3m$ structure.²⁴ Rietveld refinement (utilizing FullProf software) is performed introducing mix phase and refining atomic positions, cell parameter, B_{iso}, shape parameter, occupancies etc.⁵⁶ Refinement analysis of the Bragg scattered TiCoSb phases provides exhaustive information on the long-range order in the host phase along with defects and disorder in the synthesized HH alloy structure. Presence of CoTi and CoSb phases, obtained from mixed-phase Rietveld analysis of XRD data is reported in the TiCoSb host matrix.56 Non-monotonic behaviour of the wt% of embedded phases with Sb concentration is found. The effect of Sb concentration on wt% of embedded phases, indicates maximum TiCoSb phase exists in x=0.02 samples. Unit cell volumes, depicted in inset of fig. 3(b), exhibit a gradual reduction with increasing Sb concentration for $0 \le x \le 0.04$, followed by an enhancement at x = 0.06. Further, decrease in occupancies of Co atom in TiCoSb matrix could be the emergence of Co vacancies within the TiCoSb matrix, discussed in previous report.⁵⁶

Debye-Waller factor (B_{iso}) of synthesized samples is estimated from Rietveld refinement method. B_{iso} , estimated from the XRD describes the attenuation of X-ray scattering due to thermal vibration and accounts the displacements of atoms from their mean positions due to vibrations.⁵⁸ Thermal vibration is correlated with the crystal defects (such as vacancies, interstitials, and dislocations) and influences atomic displacements i.e. the estimated B_{iso} . Further, B_{iso} is related with Debye temperature (θ_D) and θ_D may be estimated using the Debye equation within harmonic approximation i.e., cubic and monoatomic structure is considered and it is expressed as,⁵⁹

$$B_{iso} = \left[\frac{6h^2}{MK_B\theta_D}\right] \left[\frac{1}{4} + \left(\frac{T}{\theta_D}\right)^2 \int_0^{\frac{\theta_D}{T}} \frac{x}{e^x - 1} dx\right]$$
(1)

where M and T are mass of the unit cell and absolute temperature respectively. θ_D refers to the temperature at which all vibrational modes become active. Effect of chemical bonding and lattice softening may alter θ_D .⁴⁹ Back et al. have revealed a lower θ_D in Te-deficient, $InTe_{1-\delta}$ samples owing to the weaker chemical bond and lattice softening effect.⁴⁹ Estimated θ_D (θ_D =356 K) is minimum for TiCoSb_{1.02} sample and maximum θ_D =447 K is reported for TiCoSb_{1.04}.⁵⁶ It is important to note that $\theta_D \sim 357$ is also reported by Skovsen et al.⁶⁰ Moreover, T. Sekimoto et al. determined θ_D , measuring longitudinal and shear velocities and reported a θ_D value of approximately 417 K.⁶¹ Hence, the estimated θ_D for synthesized TiCoSb_{1+x} samples are reliable. The characteristic



Fig. 1. (Color online). Sb concentration dependent thermal conductivity of synthesized $TiCoSb_{1+x}$ (x=0.0, 0.01, 0.02, 0.03, 0.04, 0.06) polycrystalline sample. Inset represents lattice thermal conductivity as a function of Sb concentration.

of estimated θ_D for synthesized TiCoSb_{1+x} samples i.e. reduction in θ_D with increasing Sb concentration for $0.0 \le x \le 0.02$ and increase in θ_D for $0.02 < x \le 0.06$, may be related with lattice softening. (Detailed lattice softening effect is discussed latter)

In order to explore the impact of crystalline defects on the κ of synthesized samples, $\kappa = \kappa_e + \kappa_l$ is estimated and reported. Well known Wiedemann Franz law, $\kappa_e = L\sigma T$ is utilized to estimated κ_e , where L is the Lorenz number, calculated from the S(T) data, employing the relation $L = [1.5 + exp(-|S|/116)] \times 10^{-8}$.⁶² On the other hand, κ_l is directly related with the phonon scattering mechanism viz, phonon-phonon scattering due to defects. However, according to Slack, in the limit of Umklapp scattering process, κ_l may be written as, ⁶³

$$\kappa_l = \Lambda \frac{\bar{M} \theta_D^3 \delta}{\gamma_G^2 n^{2/3} T} \tag{2}$$

Table 1. Weight percentage (wt%) of all embedded phases in synthesized samples, obtained from Rietveld refinement of XRD data along with the allocated wt% of phases, derived from the EDS result for $TiCoSb_{1+x}$ (x=0.0, 0.01, 0.02, 0.03, 0.04 and 0.06) HH polycrystalline alloys.

Sb Con.	XRD Result			EDS Result				
(A)	Volume	Wt% obtained from	m rietveld refi	nement of XRD	The allocate	The allocated wt% derived from the EDS result		
		TiCoSb	СоТі	CoSb	TiCoSb	СоТі	CoSb	V _{Co}
0.00	203.72	97.4	2.5	0.1	97	3	0	0
0.01	203.70	98.49	1.24	0.27	98.56	1.46	0	0.5
0.02	203.65	98.76	0.72	0.52	99.1	0.9	0	0.7
0.03	203.62	98.63	0.6	0.77				-
0.04	203.55	97.94	0.56	1.5	98.22	0	1.78	2
0.06	203.75	96.4	0.2	3.4	96.50	0	3.5	

where, \overline{M} , n and δ^3 are average atomic mass, number of atoms, and volume per atom in the unit cell, respectively. A is a physical constant (~ 3.1×10^{-6}). γ_G is the Gruneisen parameter and depends on the stoichiometry of the constituent elements. It is crucial to highlight that here we are dealing with TiCoSb_{1+x} system with a minute variation of x. So we consider the γ_G of pristine TiCoSb at room temperature, i.e., 2.13.⁴⁶ Characteristics of κ as a function of Sb concentration at room within TiCoSb matrix in minute scale. As expected, EDS data indicates a slight deviation in atomic percentages from the designed values (suppelementary) due to formation of embedded phases. Attempt is taken to compare the atomic percentages, derived from the EDS results and weight percentage, as obtained through the mixed-phase Rietveld refinement of XRD data. The allocated phase percentage of embedded phases, TiCo and CoSb (wt%) derived from the



Fig. 2. Scanning Electron microscopic images of the synthesized $TiCoSb_{1+x}$ samples. Distinguishable variation in TiCoSb matrix is evidence of the embedded phases in synthesized alloy.

temperature is depicted in fig. 1. A non-monotonous variation of κ with Sb concentration is observed, where κ initially decreases with an increase in Sb concentration up to x=0.02. However, a further increase in Sb concentration leads to gradual increase in κ . The detailed explanation of this typical behaviour of κ as a function of Sb concentration is provided latter. Below we present and analyze our results critically in different sub-section one by one.

A. Secondary electron microscope and Energydispersive X-ray Spectroscopy (EDS)

Microstructural and elemental analysis of all the TiCoSb_{1+x} (x=0, 0.01, 0.02, 0.03, 0.04, 0.06) HH alloys are carried out using scanning electron microscope and energy-dispersive X-ray spectroscopy (EDS), respectively (EDS results are given in suppelemental article). Figure 2 and Table 1 display results, demonstrating the formation of embedded phases in the TiCoSb matrix. The shining spot within the TiCoSb matrix (dark area) may suggest the presence of the embedded phases

EDS result nicely matched with the wt% of phases, obtained from XRD utilizing Rietveld refinement. The SEM and EDS results confirm the presence of embedded phases and Covacancies in the TiCoSb matrix and support the refinement results.

B. X-ray absorption fine structure spectroscopy: Investigation of short range order

The most powerful experimental method for gaining information about the atomic coordination around a particular atom, (viz. crystalline order or disorder, atomic defect) is the X-ray absorption fine structure spectroscopy (XAFS) technique using a tunable photon source, viz. the synchrotron radiation.⁶⁴ The XAFS data can be differentiated into two parts: (i) X-ray absorption near edge structure (XANES) reflects electronic features (e.g.-valance state) that are strongly influenced by the type of coordination atoms, and (ii) Extended X-ray Absorption Fine Structure (EXAFS) reflects

the local periodicity for a wide range of neighbouring atoms. ⁶⁵ Below we elaborate these issues sequentially.

i. X-ray absorption near edge structure (XANES)

The electronic configuration of Co in TiCoSb system is: [Ar] $3d^94s^{0.24}$ There are two different types of transition are allowed, shown in fig. 3(a). First, the excitation of the 1s electron to the unoccupied 4p level as the final state, gives Co

K-edge spectrum in XANES region [fig. 3(a)]. Second, transition from any occupied state to continuum gives EXAFS spectra, accomodate information of periodic arrangement of atoms in sort range. It is essential to mention that the empty 3d and 4s orbitals, lying below the 4p level could provide convenient holes for the excited core electrons,. However, $s \rightarrow d$ (1s \rightarrow 3d) and $s \rightarrow s$ (1s \rightarrow 4s) transitions are forbidden owing to the quantum selection rules, i.e; only $\Delta l = \pm 1$ transition is allowed [fig. 3(a)].⁶⁶ Therefore, the 1s \rightarrow 4p



Fig. 3. (Color online). (a) Allowed transition for Co K-edge spectrum. (b) Normalized XANES spectra of synthesized TiCoSb_{1+x} polycrystalline samples at Co-K edge. Inset shows (lower) 1st derivative of edge jump and (upper) volume obtained from XRD data of the TiCoSb_{1+x} synthesized samples. (c) Fitted XANES spectra for each TiCoSb_{1+x} samples at Co-K edge. (d) Full Width at Half Maxima (FWHM) as function Sb concentration, obtained from Raman spectroscopy and XANES spectra. Inset represents the variation of FWHM with Sb concentrations, obtained from XRD of TiCoSb_{1+x}.

transition becomes the only pathway to excite 1s electrons to the higher levels [fig. 3(a)]. Figure 3(b) shows the XANES spectra of TiCoSb_{1+x} at Co K-edges. Noteworthy, a significant shift of the Co K-edge towards lower photon energy is observed (clearly visible from 1st derivitive of edge spectra [Insets of fig. 4(b)], with the addition of Sb concentration, which manifests the change in the Co oxidation state. 67, 68 A shift ~2 eV is obtained owing to the change in the oxidation state of Co in TiCoSb_{1+x} samples for $0 \le x \le 0.04$. The shift towards the lower photon energy is due to the screening effect with a decrease in the average valence state of Co ions, i.e., an increase in the overall negative charge of the atom.67, 68 It causes due to increase of Co vacancy in TiCoSb_{1+x} samples. In order to investigate Co K-edge spectra quantatively XANES region is fitted with one arctangent step function and a pseudovoigt peak shape function [fig. 3(c)], accommodating the electric transition from 1s to continuum states and the transition to the unoccupied states respectively. The fig. 3(d) represents the FWHM of the white line for the Co K-edge XANES spectra for all the synthesized samples. The FWHM of the white line decreases up to x = 0.02, indicate the decrease in local disorder around the Co atom, whereas, higher value of FWHM for x = 0.03 to 0.06 samples is the manifestation of higher disorder.⁶⁹ It is noteworthy to mention that, FWHM of the most intense peak i.e. (200) peak of PXRD (Powder XRD) also shows similar trends. Therefore, the structural model is in good agreement with the long range order investigated by the PXRD measurement.56

ii. Extended X-ray absorption fine structure (EXAFS)

For the EXAFS analysis, the oscillation part of the measured absorption co-efficient $[\mu(E)]$ is converted into the fine structure-function ($\chi(E)$) using the following equation⁷⁰

$$\chi(E) = \frac{\mu(E) - \mu(E_0)}{\Delta \mu(E_0)}$$
(3)

where E_0 is the threshold energy of transition, $\Delta \mu_0(E_0)$ is edge step and $\mu_0(E)$ is smooth background function as the absorption of an isolated atom. Analysis in k-space is performed by converting the fine structure function of absorption co-efficient $\chi(E)$ to k-space $\chi(k)$ using the following relation⁷⁰

$$k = \sqrt{2m_e(E - E_0)\hbar^2} \tag{4}$$

where m_e is the mass of the electron, $\chi(k)$ is weighted by k^2 to amplify oscillations at high k and corresponding fittings are plotted in fig. 4(a). The $k^2\chi(k)$ function is Fourier transformed to real space (R-space) using the ARTEMIS software package [fig. 4(b)].⁷¹ $\chi(R)$ versus R (radial distance) plots [fig. 4(b)] are used for further analysis. Crystallographic inputs of the TiCoSb phase are accounted for the fitting of the spectra. Fitting in the R space is performed between 1 to 4.5 Å. The Fourier transform is carried out with multiple of k^2 -weight. The quality of the fit is measured by minimizing the

Scattering Path	Degeneracy	R _{eff}	Rank	Type of Scattering
at Co-k edge				6
@ Sb8.1 @	4.00	2.552	100	Single
@ Ti3.1 @	4.00	2.552	80.09	Single
@ Sb8.1 Ti3.1 @	24.00	4.025	10.36	Other double
@ Co5.1 @	12.00	4.167	64.65	Single
@ Sb8.1 Sb10.1 @	12.00	4.636	6.63	Other double
@ Sb8.1 Co5.1 @	24.00	4.636	20.31	Other double
@ Ti3.1 Ti0.1 @	12.00	4.636	7.55	Other double
@ Ti3.1 Co5.1 @	24.00	4.636	20.69	Other double
@ Sb8.2 @	12.00	4.887	63.27	Single
@ Ti3.2 @	12.00	4.887	51.26	Single

Table. 2. Representation of all scattering paths at Co-k edge of the synthesized $TiCoSb_{1+x}(x=0.0, 0.01, 0.02, 0.03, 0.04 \text{ and } 0.06)$ with their degeneracy, scattering length, rank and type of scattering. Highlighted paths are included in the analysis during fitting.



Fig. 4. (Color online). (a) k^2 -weighted derivatives, and (b) radial distributions of Co K-edge X-ray absorption spectra surrounding Co atom of the synthesized TiCoSb_{1+x} (x=0.0, 0.01, 0.02, 0.03, 0.04 and 0.06) HH samples, (open circles and red lines are respectively the experimental and fitted curves).



Fig. 5. (Color online). Schematic illustrations for the sequential construction of different types of scattering effect.

statistical parameter, known as R-factor (R_f). R_f is defined by the following equation^{70, 72}

$$R = \frac{\sum_{j=min}^{max} [Re\left(\chi_{d}(r_{j}) - \chi_{t}(r_{j})\right)^{2} + Im(\chi_{d}(r_{j}) - \chi_{t}(r_{j}))^{2}]}{\sum_{j=min}^{max} [Re\left(\chi_{d}(r_{j})\right)^{2} + Im\left(\chi_{d}(r_{j})\right)^{2}]}.$$
 (5)

Four path parameters (S_{0}^{2} = amplitude reduction factor, Δr = change in half path length, ΔE_{0} = energy shift, σ^{2} = mean square displacement) are taken into consideration to fit the experimental data with FEFF generated modelling using ARTEMIS, which includes IFEFFIT integration.⁷¹ The scattering paths with there ranks are listed in the Table 2 and a visualization of scattering effect is shown in fig. 5. It is important to mention that only one multi scattering paths are discarded because of low rank. The details about the path with the rank for TiCoSb is presented in the Table 2. The number of free variables (N_{free}) is always kept below the upper limit,

set by the Nyquist theorem (N_{free} $\leq N_{Nyquist} = 2\Delta k\Delta r/\pi + 1$), by assuming the same E_0 for all the paths where Δr is the width of the filter windows in the R-space and Δk is the actual interval of the fit in the k-space.⁷³ The overall value of the Rfactor is then minimized to establish the quality of the fitting. Here, the total number of neighbors for each shell is kept constant with the intention of minimizing N_{free}. The Fourier transforms show well defined peaks around 2.5 and 4.2 Å [fig. 4(b)]. These correspond to the single scattering in nearest neighbour shell i.e. coordination shell and second nearest neighbour shell, respectively. The absorber Co is coordinated tetrahedral by 4 Sb and 4 Ti atoms (Reff = 2.5 Å) and dodecahedral by 12 Co (Reff = 4.167 Å). Crucial to mention that, a splitting of the first peak is observed in the Fourier transformed (R = 2-2.5 Å) [fig. 4(b)] data, due to different scattering phases of Ti and Sb atoms. In the region between those three main peaks i.e. R~ 2.5-3.5 Å, small peaks appear due to the contribution of multiple scattering. The reliability

Table 3. The fitting parameters of EXAFS curves for the synthesized TiCoSb_{1+x} (x=0.0, 0.01, 0.02, 0.03, 0.04, 0.06) HH samples obtained at the Co K-edge. R_{Co-Sb}, R_{Co-Ti}, σ_{Sb}^2 , σ_{Ti}^2 and Happiness are Co-Sb bond length, Co-Ti bond length, Debye-Waller factors for 1st shell, and 2nd shell and Happiness of the fits, respectively.

Sb Concentration	$R_{Co-Sb}(\text{\AA})$	R _{Co-Ti} (Å)	σ_{Sb}^2	σ_{Ti}^2	Happiness
0.00	2.543±0.004	2.541±0.008	0.0034±5.3989E-4	0.0104±0.00084	100.0
0.01	2.539±0.003	2.530±0.006	0.0029±5.2486E-4	0.0110±0.00105	95.77
0.02	2.534±0.003	2.506±0.005	0.0030±4.7079E-4	0.0086±0.00261	97.00
0.03	2.532±0.004	2.489±0.011	0.0025±5.3469E-4	0.0106±0.00107	98.45
0.04	2.542±0.003	2.486±0.006	0.0027±5.0786E-4	0.0110±0.00104	93.14
0.06	2.538±0.005	2.537±0.009	0.0026±6.1525E-4	0.0110±0.00115	89.44

of the fits is asserted by the small values of the σ^2 and R factors (Table 3). Nevertheless, the comparison of the fitted and experimental data in fig. 4(a) and 4(b) also confirms the goodness of the fits. EXAFS analysis opens the path to investigate the effect of Sb on the local geometry of TiCoSb_{1+x} HH alloy. It is observed that there is an obvious effect in bond lengths due to the addition of Sb in TiCoSb. The change in the bond length is depicted in Table 3. In the 1st shell, there is a significant change in Co-Ti length from 2.541Å (for x=0.00) to 2.489 Å (for x=0.04), and in the 2nd shell an insignificant change in Co-Sb distance from 2.543Å (for x=0.00) to 2.532Å (for x=0.03) are observed. The results clearly indicate a change in local structural parameters around Co in TiCoSb_{1+x} (x=0, 0.01, 0.02, 0.03, 0.04, and 0.06) samples. The EXAFS results suggest that Sb doping reduces the 1st and 2nd shell (mainly the 1st shell) volume due to the existence of Co vacancy in the samples. Notable, the Debye-Waller factors σ^2 , obtained from fitting are approximately 1 x 10⁻² Å² for the 1st

shell (Co-Ti) and $0.3 \times 10^{-3} \text{ Å}^2$ for the 2nd shell (Co-Sb). Lower value of Debye-Waller factors (of EXAFS) and insignificant change in volume of the 2nd shell, indicate that in the TiCoSb based HH alloy the crystalline order in the short range is mainly preserved from the contribution of 2nd shell (i.e., Co-Sb).

C. Raman spectroscopy measurements

For the first time, we performed a comprehensive analysis of the vibrational spectroscopy of the TiCoSb-based HH alloy. The Raman spectra of TiCoSb_{1+x} samples confirms single-phase nature of the synthesized samples. No evidence of embedded phases is found in the measured frequency range. Experimental spectrum exhibits three prominent peaks located at 230 cm⁻¹, 264 cm⁻¹, and 318 cm⁻¹ [fig. 6(a)]. Popovic⁷⁴ et al. and Mestres⁷⁵ et al. both have categorized the first two peaks as TO-modes and third peak at 318 cm⁻¹ as a LO-mode for



Fig. 6. (Color online). (a) Raman spectroscopy of $TiCoSb_{1+x}$ with indexing different types of vibrational modes. (b) Schematic diagram of lattice vibration for LO1, TO1 (b-i) and LO2, TO2 (b-ii) modes in TiCoSb sample. The arrow is nearly propositional to the atomic displacement during vibration. The green, blue and grey color balls represent Sb, Co and Ti atoms respectively. (c) Representation of origin of polar nature in TiCoSb material. The arrangement of $(TiSb)^{+1}$ and Co^{-1} charged planes within the crystal structure, results in an electric dipole moment.

similar types of HH alloy. However, computational analysis by Hermet et al. unequivocally confirms the identification of the TO2 and LO2 modes at around 264 and 318 cm^{-1,76} Regarding the LO1 mode, the calculations indicate that the intrinsic scattering efficiency is comparable to that of the TO1 line. Hence, LO1 and TO1 overlap with each other in Raman spectroscopy (RS). Therefore, the first experimental peak at 228 cm⁻¹ for RS of TiCoSb_{1+x} may be recognized as a combination of the TO1 and LO1 modes. The other two peaks at 264 cm⁻¹ and 318 cm⁻¹ are identified as TO2 and LO2 modes, respectively. Schematic diagram of lattice vibration for LO1, TO1 (upper) and LO2, TO2 (lower) modes in TiCoSb sample are depicted in fig. 6(b). It is crucial to note that the splitting of TO and LO modes is observed for the synthesized TiCoSb_{1+x} samples [fig. 6(a)]. The frequency of TO2 and LO2 is significantly different, but the frequencies of TO1 and LO1 are indistinguishable. However, it is crucial to note that the splitting between the TO and LO modes is one of the signatures of polar materials.77, 78 TiCoSb-based HH materials may be recognized as polar materials. In these compounds, the electronic configuration and the oxidation states of the constituent elements play a crucial role in determining their properties, including polarity. The stable electronic configuration is a result of the specific oxidation states of Ti, Co, and Sb in TiCoSb. The oxidation states are as follows: Ti is in the +4 oxidation state, Co is in the -1 oxidation state, and Sb is in the -3 oxidation state. Therefore, TiCoSb structure can be considered as alternating arrangement of negatively charged Co⁻¹ planes and positively charged (TiSb)⁺¹ planes [fig. 6(c)].⁷⁹ The arrangement of these charged planes within the crystal structure results in an electric dipole moment. This dipole moment arises from the nonuniform distribution of charge along specific crystallographic directions. Therefore, the ionic interaction within the Co⁻¹ and (TiSb)⁺¹ planes is essential. The alternating Co⁻¹ and (TiSb)⁺¹ planes create an electric polarity within the material [fig. 6(c)].⁷⁹ This non-uniform charge distribution can be quantitatively described in terms of the polarization of material. The polarity may have significant implications for the properties (e.g. κ) and behaviour of material (discussed latter).

The position of highest intense peak, as obtained in RS measurements for TiCoSb_{1+x} synthesized samples as a function of Sb concentration is illustrated in fig. 7. From fig. 6(a) (inset) and fig. 7, it is evident that as the Sb concentration increases up to x=0.02 ($0 \le x \le 0.02$), the predominant peak (TO2 mode) undergoes a shift towards lower frequencies, indicating a red shift. As the Sb concentration continues to rise ($0.02 < x \le 0.04$), the observed shift moves towards higher frequencies, i.e. a blue shift. Basically, red shift indicates the

frequency of phonons interacting with the incident photon is decreased, while blue shift suggests increase in frequency. A shift toward higher frequencies (red shift) signifies a reduction in compressive strain, while a shift towards lower frequencies (blue) indicates an increase in compressive strain.⁸⁰ Specifically, the presence of embedded phases contributes to an increase in compressive strain within the TiCoSb matrix. The behaviour nicely corroborates the crystalline strain obtained from the PXRD measurement for the identical samples.⁵⁶ It is important to highlight that changes in



Fig. 7. (Color online). Variation of position of highest intense peak of Raman spectroscopy and estimated strain (ε) from X-ray diffraction with Sb concentration of synthesized TiCoSb_{1+x} HH polycrystalline samples. The diagram bellow the figure represents effect of strain on group velocity (v_a) in crystal lattice.

crystalline strain can influence κ of the system. Internal compressive strain may be induced by lattice defects and embedded phases, that locally modify phonon frequencies within the material and in principle it may lead to lattice stiffness.⁴⁷ Several cases are investigated where a modification in κ is attributed to tuning the lattice stiffness (or lattice softening), correlated with alloying or the introduction of point defects.⁴⁷ In certain instances, it is anticipated that adjustment of the lattice stiffness have a more significant impact on κ_l than micro/nanostructural scattering.^{81, 82} κ_l in materials may be defined as ⁸³

$$\kappa_l = \frac{1}{3} \int_0^{\omega_{max}} v_g^2 C_s \tau \, d\omega \tag{6}$$

where C_s is the heat capacity, v_g is the group velocity of phonon through the matrix, and τ is the phonon relaxation time. Equation 6 may be written as, considering phonon–phonon scattering dominate: ^{81,82}

$$\kappa_l = \frac{(6\pi^2)^{2/3}\overline{M}}{V^{2/3}4\pi^2\gamma^2} \frac{\langle v_g^3 \rangle}{T} = A \frac{\langle v_g^3 \rangle}{T}$$
(7)



Fig. 8. (Color online). Multiple-peak fitting of Raman spectroscopy of $TiCoSb_{1+x}$ (x=0.0, 0.01, 0.02, 0.03, 0.04 and 0.06) with Lorentzian function for LO1, TO1, LO2 and TO2 modes.

where $\langle v_a^3 \rangle$ is denoted as average group velocity over the Brilluon Zone. In this article, the detailed study and explanations are involved to emphasise the sensitivity of κ_1 to lattice stiffness, which manifests through a cubic dependence on phonon velocity. Hanus et al. have reported a roughly 50% decrease in κ (from 200 Wm⁻¹K⁻¹ to 100 Wm⁻¹K⁻¹) for single crystal Si to polycrystalline Si, employing the Callaway-type thermal transport model while solely considering the lattice softening effect.⁴⁷ In this scenario, v_a decreases from 5830 m/s to 4440 m/s.⁴⁷ Further, 7% reduction in v_g by tuning internal strain results a reduction in $\kappa \sim 21\%$ for PbTe.⁴⁷ Thus, lattice softening emerges as a promising pathway for enhancing TE efficiency, enabling a decrease in κ_1 without the requirement of a high density of defects that typically induces electron scattering. In the TiCoSb_{1+x} synthesized samples, increase in Sb concentration for $0 \le x \le 0.02$, results an enhancement in tensile strain (i.e. decrease in compressive strain) leads to an increase in lattice softening (fig. 7). Increase in lattice softening corresponds to decrease in the group velocity (v_g) , concomitantly decrease in κ_L , according to eq. 7. Hence, decrease of compressive strain for $0 \le x \le 0.02$ of TiCoSb_{1+x} synthesized samples, indicates reduction in κ (fig. 1). And for $(0.02 < x \le 0.04)$ enhancement in κ is attributed to the decrease in lattice softening owing to the increase in compressive strain.

In order to study the effect of Sb concentration on the crystalline order of $TiCoSb_{1+x}$ samples, the RS peak around

230 cm⁻¹ is fitted with two Lorentzian type functions to accommodate the TO1 and LO1 modes. The fitting is shown in fig. 8. An anomalous behaviour of the intensity of LO1 and TO1 modes with Sb concentration is observed (fig. 8 and fig. 9). At x=0, the dominant mode is TO1. The intensity of the TO1 mode decreases with Sb concentration up to x=0.02, after which it exhibits an increasing trend. Conversely, the LO1 mode demonstrates an opposite behaviour. Noteworthy, both LO1 and TO1 modes equally dominate at x=0.02. This



Fig. 9. (Color online). Variation in intensity of TO1, LO1 mode of Raman spectroscopy with Sb concentration for synthesized $TiCoSb_{1+x}$ (x=0.0, 0.01, 0.02, 0.03, 0.04, 0.06) HH alloys. LO1/TO1 define the intensity of LO1 relative to TO1 mode.

behaviour could be associated with lattice strain and crystalline order. As the concentration of Sb increases up to x=0.02, the lattice becomes soften owing to the reduction in compressive strain. Lattice softening leads to a decrease in the TO1 mode and an enhancement in the LO1 mode. Further increase in Sb (0.02 < x < 0.06) concentration introduces lattice stiffness, which increases TO1 mode and reduce LO1 mode.

The LO and TO phonon modes have different frequencies due to the behaviour of phonon during vibration of crystal lattice planes in polar crystal. The long range electric field caused by ionic polarization specifically affects the LO phonon vibration.⁵² This long range electric field alters the energy associated with the LO mode, leads to a frequency difference between LO and TO. The characteristics of phonons in crystals may be explained by using the theoretical model proposed by Born and Huang.⁸⁴ The model takes into account the interactions between atoms, including charge carriers and vibrations. The model clearly defines the influence of interactions on the vibrational modes and frequencies in a crystal lattice. The model relation between LO and TO is described as,⁷⁸

$$\omega_{LO}^{2} = \omega_{TO}^{2} + \Psi(q) \frac{|q|^{2}}{\Omega} \left(\sum_{a} \frac{e_{q.Z_{a}.e_{LO}}^{a}}{\sqrt{M_{a}}} \right)^{2}$$
(8)

where, ω_{L0} and ω_{T0} represent the frequencies of the LO and TO phonon modes, respectively. eq represents a unit vector along the momentum direction of q, e_{LO}^{a} signifies the eigenvector of the dynamical matrix of the LO mode at $|q| \rightarrow 0$. $M_{\rm a}$ is the mass of atom 'a' in the unit cell, and $Z_{\rm a}$ represents the Born effective charge of atom 'a'. The Born effective charge characterizes the change in polarization in response to the displacement of the atom owing to lattice vibration. Additionally, $\Psi(q)$ represents the Coulomb interaction in Fourier space. In a polar material the distribution of charges within the material changes during lattice vibration. This change in the charge distribution results in a shift in the overall electric polarization of the material. In other words, the material becomes polarized in response to the displacement of atoms. Hence Z_a is nonzero for polar material, and LO-TO splitting is observed. It is essential to recognize that, Co atoms are located at the center of both Ti and Sb tetrahedrons. The opposite vibration of Ti and Sb with respect to Co [fig. 6(bii)] involves relatively larger chemical bonding forces, correspond to the higher energy optical phonon branches. Further, the vibration is related with change in (TiSb)⁺¹ and Co⁻¹ planes in opposite directions [fig. 6(b-ii)]. Consequently, Za is substantial for this specific vibration [fig. 6(b-ii)]. This phenomenon causes significantly large LO-TO splitting in this specific vibration. Presence of defects and disorder may also significantly influence the LO-TO splitting [discussed latter].

Figure 10 depicts the frequency difference ($\Delta \omega_2 = \omega_{LO2} - \omega_{TO2}$) between the TO2 and LO2 modes of Raman spectroscopy for TiCoSb_{1+x} with the Sb concentration. The non-monotonic behaviour of $\Delta \omega_2$ with Sb concentration (x) is observed. The value $\Delta \omega_2$ increases up to x = 0.02 and thereafter decreases. The increase of $\Delta \omega_2$ may be associated with the improved crystalline order and decrease of crystalline strain (compressive). A gradual decrease in compressive strain of TiCoSb_{1+x} (for $0 \le x \le 0.02$) samples (fig. 7) induces scattering phase space and concomitantly decreases κ_1 .⁸⁵ Yang et al. have reported an elevation in the frequency difference



Fig. 10. (Color online). Frequency difference $\Delta\omega_2$ (LO2-TO2 splitting) of synthesized TiCoSb_{1+x} HH alloy as function Sb concentration.

between the LO and TO modes in CaO due to massive increase in scattering phase space, related to change in strain from compressive to tensile.⁸⁵ However, the decrease of $\Delta\omega_2$ for x > 0.02 seems to be related with screening effect due to the Co vacancy.⁵² Co vacancy can induce free carrier in the system, as reported in our previous literature⁵⁶ and supported by the EXAFS study in preceding paragraph. Presence of free carriers and concomitant screening effect may modify both the electron-LO phonon interaction and the dispersion characteristic of the LO optical phonon. According to the Thomas-Fermi approximation, if screening effect is accounted then the Coulomb interaction in the q space, is defined as ^{52, 78}

$$\Psi(q) = \frac{e^2 r_{screening}^2}{\varepsilon_{\infty}(1+|q|^2 r_{screening}^2)}$$
(9)

where $r_{screening}^2$ is the Thomas-Fermi screening length (or Debye length), and is defined as, ⁵²

$$r_{screening}^2 = \frac{ek_BT}{ne^2}$$
(10)

where, k_B is the Boltzmann constant and n represents carrier concentration. Higher n leads to smaller $r_{screening}$, and smaller r_{screening} signifies better screening effect. Additionally, according to Eq.9, in the limit of $q \rightarrow 0$ a smaller $r_{screening}$ leads to reduced $\Psi(q)$, indicates lower splitting i.e. $\Delta\omega_2$ (Eq. 8). Further, it is noteworthy to mention that, the electric polarization fields of ions in a conductor are also diminished by a cloud of electrons⁵² i.e. increasing screening, alike to the reduction of the electric field of the nucleus inside an atom or ion due to the shielding effect. The screening increases owing to the formation of Co vacancies in TiCoSb_{1+x} for $0.02 < x \le 0.06$, as previously discussed. This heightened screening leads to a reduction in the LO2-TO2 splitting and the polarization field, consequently decrease polar optical phonon scattering. Further, decrease in polar optical phonon scattering is reflected in enhancement of κ_l with increase of Sb concentration in TiCoSb_{1+x} samples. This trend is clearly depicted in fig. 1, where κ_1 shows an upward trajectory within the range of $0.02 < x \le 0.06$ due to screening effect.52

IV. Conclusion

In this work, efforts have been employed to reveal the details of lattice vibration and concomitantly, the effects of defects and crystalline strain on the κ of TiCoSb_{1+x} (x=0.0, 0.01, 0.02, 0.03, 0.04 and 0.06) synthesized materials. It is noteworthy to mention that nature of lattice vibration is explored through Raman spectroscopy measurements and vibrational modes are reported for TiCoSb HH alloy, first time in this article. Presence of embedded phases and Co vacancies are estimated, employing mixed-phase Rietveld refinement analysis of the XRD data. SEM-EDS and XANES measurements are performed to confirm and get experimental evidence for formation of Co vacancies along with embedded phases in TiCoSb_{1+x} synthesized polycrystalline HH alloy. However, it is crucial to mention that the arrangement of nearest neighbour and average coordination number are probed through EXAFS experimental facility, primarily for TiCoSb synthesized alloy. The effect of Sb concentration on ε for TiCoSb_{1+x} synthesized samples is estimated from RS and XRD data. Lattice strain (ε) , calculated using both experimental data are nicely corroboted and minimum compressive strain is obtained for TiCoSb_{1.02}. However, presence of Co vacancies are strongly regulated by tuning Sb concentration in TiCoSb HH alloy. Lattice stiffness due to internal compressive strain in TiCoSb_{1+x} leads to a local change in phonon frequencies in the synthesized alloy and modifies the group velocity (v_a) of the phonon, resulting alteration in κ_{l} . Minimum v_{g} corresponding to lowest κ is expected for x=0.02 sample. Further, a gradual decrease in compressive strain for $0 \le x \le 0.02$ induces scattering phase space and concomitantly decreases κ_{l} . However, for 0.02 < $x \le 0.06 \kappa_1$ increases owing to an increase in compressive strain and Co vacancies. LO-TO spliting and the polarization field are reduced for $0.02 < x \le 0.06$ owing to screening effect, results from increase in Co vacancies. Hence, decrease in polar optical phonon scattering results increase in κ_1 for $0.02 < x \le 0.06$. It is noteworthy to mention that, κ_1 decreases ~47% for x=0.02 amid the synthesized TiCoSb_{1+x} HH polycrystalline alloy. Lattice softening and LO-TO splitting play a crucial role in thermal energy transport through lattice vibration, and κ_1 may be tuned through crystalline strain and Co vacancies.

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Supplemental Article

Drastic modification in thermal conductivity of TiCoSb Half-Heusler alloy: Phonon engineering by lattice softening and ionic polarization

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FIGURE S1: (Color online). Energy dispersive X-ray spectroscopy (EDS) of synthesized $TiCoSb_{1+x}$ (x = 0.00, 0.01, 0.02, 0.03, 0.04, and 0.06) Half-Heusler samples at room temperature.



Sum Spectrum

Smart Quant Results

Element	Weight %	Atomic %	Net Int.	Error %	
SbL	52.53	32.68	251.61	2.33	
TiK	21.26	33.64	176.38	3.64	
СоК	26.21	33.68	113.08	3.76	





Smart Quant Results

Element	Weight %	Atomic %	Net Int.	Error %	
SbL	52.99	33.07	269.73	2.28	
TiK	21.13	33.55	166.38	3.73	
CoK	25.88	33.38	118.09	3.73	



Sum Spectrum

Smart Quant Results

Element	Weight %	Atomic %	Net Int.	Error %	
SbL	53.14	33.21	267.04	2.31	
TiK	21.09	33.52	176.82	3.70	
CoK	25.77	33.27	114.01	3.77	





Smart Quant Results

Element	Weight %	Atomic %	Net Int.	Error %	
SbL	51.75	32.03	246.65	2.31	
TiK	21.23	33.42	157.90	3.69	
СоК	27.02	34.55	106.26	3.78	

Sum Spectrum



Smart Quant Results

Element	Weight %	Atomic %	Net Int.	Error %	
SbL	53.75	33.76	238.17	2.32	
TiK	20.76	33.16	151.67	3.75	
СоК	25.49	33.08	99.37	3.80	



Element	Weight %	Atomic %	Net Int.	Error %	
SbL	53.39	33.50	197.76	2.33	
TiK	20.25	32.33	122.55	3.80	
CoK	26.36	34.17	81.49	3.89	

EDS result analysis:

1. <u>For x=0.0</u>,

EDS data: Ti_{0.3364}Co_{0.3368}Sb_{0.3268} => TiCoSb_{0.97} => 97% (TiCoSb) + 3% CoTi

2. <u>For x=0.01</u>,

EDS data: Ti_0.3355Co_0.3338Sb_0.3307 => TiCo_0.9949Sb_0.9856 => 98.56% TiCoSb + 1.46% CoTi + $0.5\%V_{Co}$

3. <u>For x=0.02</u>,

EDS data: $Ti_{0.3352}Co_{0.3327}Sb_{0.3321} => TiCo_{0.993}Sb_{0.991} => 99.1\% TiCoSb + 0.9\% CoTi + 0.7\% V_{Co}$

4. <u>For x=0.04</u>,

EDS data: $Ti_{0.3316}Co_{0.3308}Sb_{0.3376} => Ti_{0.982}Co_{0.979}Sb => 98.22\% TiCoSb + 1.78\% CoSb + 2\% V_{Co}$

5. <u>For x=0.06</u>,

EDS data: $Ti_{0.3233}Co_{0.3417}Sb_{0.3350} => Ti_{0.965}Co_{1.02}Sb => 96.50\% TiCoSb + 3.5\% CoSb + 2\% Excess-Co$

FIGURE S2: (Color online). X-ray absorption fine spectroscopy at Co K-edge of $TiCoSb_{1+x}$ (x = 0.00, 0.01, 0.02, 0.03, 0.04 and 0.06) samples at room temperature.

